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thermoplastic	O <sub>2</sub> plasma, excimer laser	~200 - 210° C/60°	~150° C / ~30'	toluene mesitylene
thermoplastic	O <sub>2</sub> plasma, excimer laser	~150° C / 60'	~150° C / ~30'	ketones anisole
Thermoset. TCE.~50 ppm/C	O <sub>2</sub> plasma, excimer laser	~150-200° C / 60°	not required	ketones
Thermoset.	Expose to actinic radiation, then wet etch after solvent drive off	~200 - 210° C / 60'	~150° C / ~30'	mesitylene
Thermoplastic TCE ~50 ppm/C	O <sub>2</sub> plasma, excimer laser	~200 - 220° C / 60°	~150° C / ~30'	anisole
Thermoset. TCE ~50 ppm/C	CF4/0 <sub>2</sub> plasma, excimer laser	~200 - 210° C / 60'	~150° C / ~30'	mesitylene
Column 6	Column 5	Column 4	Column 3	Column 2
Comment	Etch Methods	Bonding Temp/Time	Solvent Drive Off Temp/Time	Solvent



